

140 COMMERCE DRIVE MONTGOMERYVILLE, PA 18936-1013

PHONE: (215) 631-9840 FAX: (215) 631-9855

MS2267

RF & MICROWAVE TRANSISTORS AVIONICS APPLICATIONS

Features

- 960 1215MHz
- 50 VOLTS
- 5:1 VSWR CAPABILITY @ RATED CONDITIONS
- INPUT/OUTPUT MATCHING
- P_{OUT} = 250 WATTS
- $G_P = 8.0 \text{ dB MINIMUM}$
- COMMON BASE CONFIGURATION

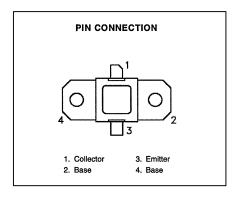
.400 x .400 2L flanged (M214) hermetically sealed

DESCRIPTION:

The MS2267 is a high power Class C NPN transistor specifically designed for TACAN/DME applications.

This device is capable of operation under moderate pulse width and duty cycles. Low thermal resistance and computerized automatic wire bonding techniques ensure high reliability and product consistency.

The MS2267 utilizes an emitter ballasted die geometry capable of operating into a 5:1 VSWR @ 1.0 dB overdrive.



ABSOLUTE MAXIMUM RATINGS (Tcase = 25° C)

Symbol	Parameter	Value	Unit
P _{DISS}	Power Dissipation* (T _C ≤ 90°C)	575	W
Ic	Device Current*	20	Α
Vcc	Collector-Supply Voltage*	50	V
T J	Junction Temperature (Pulsed RF Operation)	250	°C
T _{STG}	Storage Temperature	-65 to +200	°C

Thermal Data

R _{TH(J-C)}	Junction-case Thermal Resistance* (1)	0.28	°C/W
----------------------	---------------------------------------	------	------

^{*} Applies only to rated RF amplifier operation

⁽¹⁾ Infra-red scan of hot spot junction temperature at rated RF operating conditions



MS2267

ELECTRICAL SPECIFICATIONS (Tcase = 25°C) STATIC

Symbol	Toot Conditions		Value			
Symbol	Test Conditions		Min.	Тур.	Max.	Unit
BV _{CBO}	I _C = 35mA	I _E = 0 mA	65			V
BV _{EBO}	I _E = 15mA	$I_C = 0 \text{ mA}$	4.0			V
BV _{CES}	I _C = 25mA	I _B = 0 mA	60			V
I _{CES}	V _{BE} = 0 V	$V_{CE} = 50V$			20	mA
h _{FE}	V _{CE} = 5V	I _C = 1A	10			

DYNAMIC

Symbol	Test Conditions			Value			
Symbol Test Conditions		Min.	Тур.	Max.	Unit		
P _{out}	f = 960 - 1215MHz	P _{IN} = 40W	$V_{CC} = 50V$	250	295		W
ης	f = 960 - 1215MHz	$P_{IN} = 40W$	$V_{CC} = 50V$	38	44		%
G _P	f = 960 - 1215MHz	P _{IN} = 40W	$V_{CC} = 50V$	8.0	8.7		dB

Conditions:

Pulse width = 20 μ S

Duty Cycle = 5%

 $T_C = 25^{\circ}C$

IMPEDANCE DATA

FREQ	$Z_IN(\Omega)$	$Z_{CL}(\Omega)$
960 MHz	1.0 + j3.5	1.9 – j1.8
1090MHz	4.0 + j3.5	1.6 – j0.9
1215MHz	2.2 + j2.2	1.4 – j1.1

 $P_{\text{IN}} = 40W$

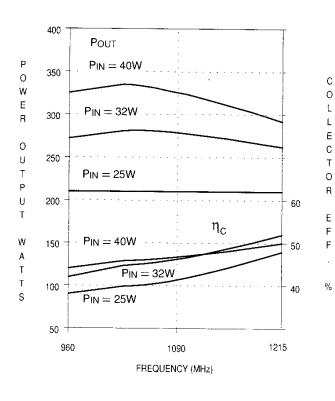
 $V_{\text{CC}} = 50V$



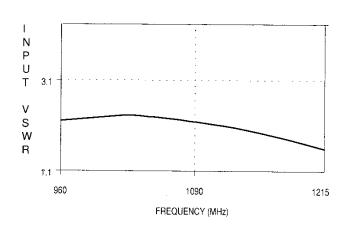
MS2267

TYPICAL PERFORMANCE

TYPICAL BROADBAND POWER AMPLIFIER



INPUT VSWR vs FREQUENCY

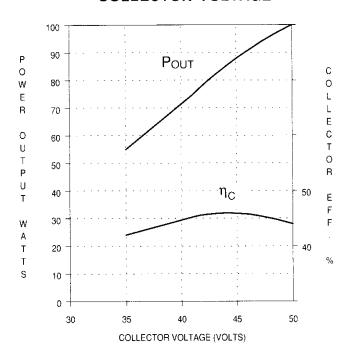






TYPICAL PERFORMANCE (CONTINUED)

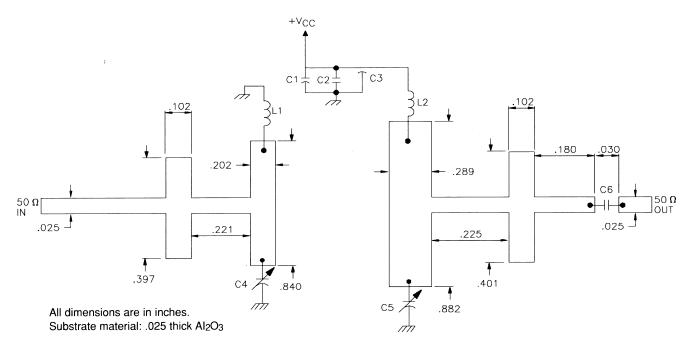
TYPICAL POWER OUTPUT & COLLECTOR EFFICIENCY vs COLLECTOR VOLTAGE





MS2267

TEST CIRCUIT



C1 : 100 μ F Electrolytic Capacitor, 63V

C2 : .1 μF Ceramic Capacitor
C3 : Feedthru Bypass SCI 712-022

C4 : Johanson 7475 Gigatrim .6 — 4.5 pF

C5 : Johanson 7475 Gigatrim .6 — 4.5 pF

C6 : D.C. Block 100 pF

L1 : #26 Wire, 4 Turn .062 I.D.





PACKAGE MECHANICAL DATA

